

Li Ning Liu

List of Publications by Year in descending order

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14
papers

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1307594

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65
citing authors

#	ARTICLE	IF	CITATIONS
1	Single $\text{In}^2\text{-Ga}_2\text{O}_3$ nanowire based lateral FinFET on Si. Applied Physics Letters, 2022, 120, .	3.3	10
2	Single $\text{In}^2\text{-Ga}_2\text{O}_3$ nanowire back-gate field-effect transistor. Semiconductor Science and Technology, 2022, 37, 085009.	2.0	3
3	Transparent dual-band ultraviolet photodetector based on graphene/p-GaN/AlGaN heterojunction. Optics Express, 2022, 30, 21349.	3.4	7
4	Strategy for Addressing the Low Quantum Efficiency of Nanowire Photodetectors. ACS Photonics, 2022, 9, 2280-2286.	6.6	3
5	Highly sensitive SWIR detector array based on nanoscale phototransistors integrated on CMOS readout. Applied Physics Letters, 2020, 117, .	3.3	8
6	Surface Passivation Using Lanthanide Oxynitrides for GaAs Metal-Oxide-Semiconductor Applications. IEEE Transactions on Electron Devices, 2019, 66, 3080-3085.	3.0	2
7	Advances in La-Based High-k Dielectrics for MOS Applications. Coatings, 2019, 9, 217.	2.6	24
8	GaAs Metal-Oxide-Semiconductor Capacitor With Nd-Based High-k Oxynitrides as Gate Dielectric and Passivation Layer. IEEE Transactions on Electron Devices, 2018, 65, 72-78.	3.0	9
9	High-performance GaAs metal-oxide-semiconductor capacitor by using NbAlON as high-k gate dielectric. Applied Physics Letters, 2017, 110, 123506.	3.3	7
10	Improved Electrical Properties and Reliability of GaAs Metal-Oxide-Semiconductor Capacitor by Using LaAlON Passivation Layer. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700180.	2.4	4
11	Improved performance of pentacene OTFT by incorporating Ti in NdON gate dielectric. , 2017, , .		1
12	Effects of Y incorporation in TaON gate dielectric on electrical performance of GaAs metal-oxide-semiconductor capacitor. Physica Status Solidi - Rapid Research Letters, 2016, 10, 703-707.	2.4	6
13	Passivation of oxide traps in gallium arsenide (semiconductor) metal-oxide-semiconductor capacitor with high-k dielectric by using fluorine incorporation. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 050601.	1.2	12
14	Passivation of oxide traps and interface states in GaAs metal-oxide-semiconductor capacitor by LaTaON passivation layer and fluorine incorporation. Applied Physics Letters, 2015, 107, .	3.3	16